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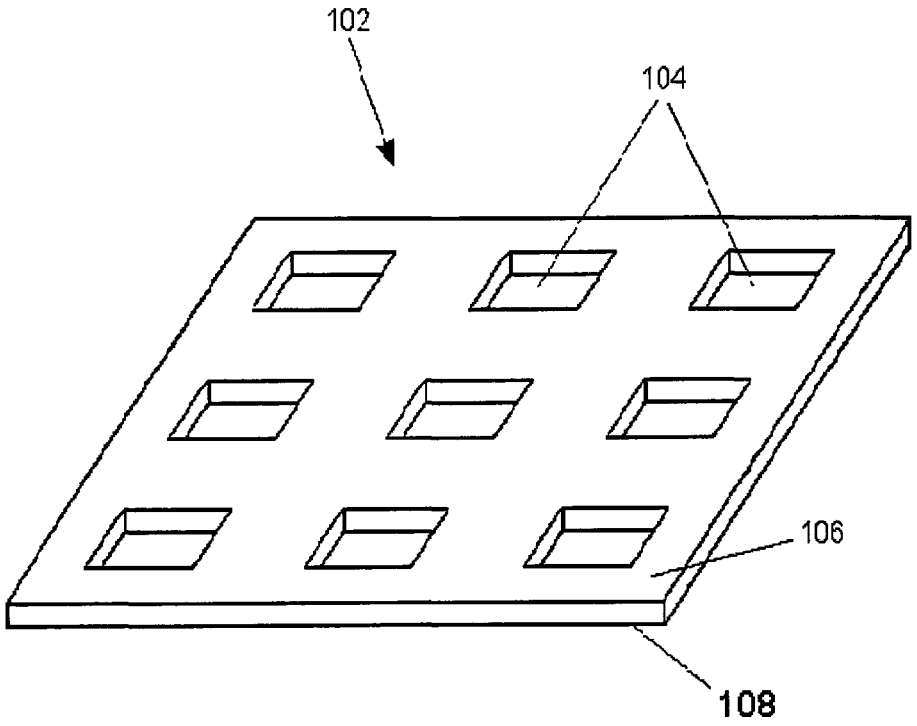
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(54) Title: INTEGRATED CORE MICROELECTRONIC PACKAGE



(57) Abstract: A microelectronic package including a microelectronic die disposed within an opening in a microelectronic packaging core, wherein an encapsulation material is disposed within portions of the opening not occupied by the microelectronic die. Build-up layers of dielectric materials and conductive traces are then fabricated on the microelectronic die, the encapsulant material, and the microelectronic package core to form the microelectronic package.

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